

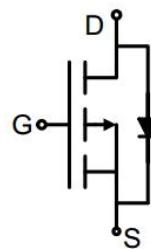
P-Channel Enhancement Mode Power MOSFET

Description

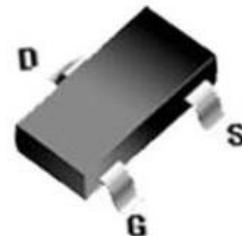
The 3401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} -30V
- I_D (at $V_{GS} = -10V$) -4.2A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 55mΩ
- $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) < 69mΩ
- $R_{DS(ON)}$ (at $V_{GS} = -2.5V$) < 102mΩ
- 100% Avalanche Tested
- RoHS Compliant



Schematic diagram



SOT-23

Application

- Power switch
- DC/DC converters

Ordering Information

| Device | Package | Marking | Packaging |
|--------|---------|---------|--------------|
| 3401 | SOT-23 | 3401 | 3000pcs/Reel |

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

| Parameter | Symbol | Value | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Continuous Drain Current | I_D | -4.2 | A |
| Pulsed Drain Current (note1) | I_{DM} | -17 | A |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Power Dissipation | P_D | 1.2 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 To 150 | °C |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|---|------------|-------|------|
| Thermal Resistance, Junction-to-Ambient | R_{thJA} | 104 | °C/W |

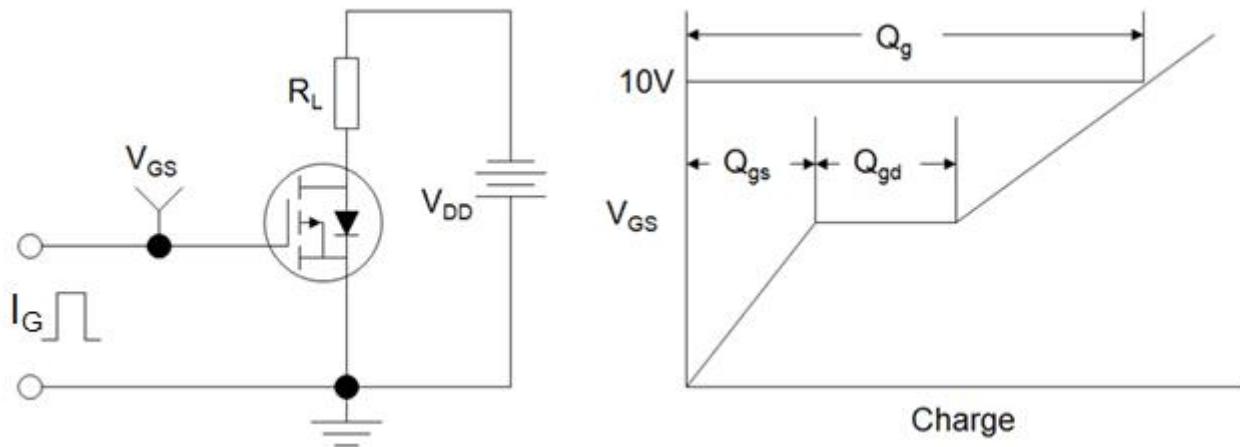
Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

| Parameter | Symbol | Test Conditions | Value | | | Unit |
|--|-----------------------------|---|-------|------|-----------|------------------|
| | | | Min. | Typ. | Max. | |
| Static Parameters | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$ | -30 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = 0\text{V}$ | -- | -- | -1 | μA |
| Gate-Source Leakage | I_{GSS} | $V_{\text{GS}} = \pm 12\text{V}$ | -- | -- | ± 100 | nA |
| Gate-Source Threshold Voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$ | -0.6 | -0.8 | -1.3 | V |
| Drain-Source On-Resistance | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}} = -10\text{V}, I_D = -4\text{A}$ | -- | 42 | 55 | $\text{m}\Omega$ |
| | | $V_{\text{GS}} = -4.5\text{V}, I_D = -4\text{A}$ | -- | 49 | 69 | |
| | | $V_{\text{GS}} = -2.5\text{V}, I_D = -2\text{A}$ | -- | 64 | 102 | |
| Forward Transconductance | g_{FS} | $V_{\text{DS}} = -5\text{V}, I_D = -4\text{A}$ | -- | 10 | -- | S |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = -15\text{V}, f = 1.0\text{MHz}$ | -- | 756 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 68 | -- | |
| Reverse Transfer Capacitance | C_{rss} | | -- | 60 | -- | |
| Total Gate Charge | Q_g | $V_{\text{DD}} = -15\text{V}, I_D = -4\text{A}, V_{\text{GS}} = -4.5\text{V}$ | -- | 8.5 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 1.8 | -- | |
| Gate-Drain Charge | Q_{gd} | | -- | 2.7 | -- | |
| Turn-on Delay Time | $t_{\text{d}(\text{on})}$ | $V_{\text{DD}} = -15\text{V}, I_D = -4\text{A}, R_G = 6\Omega$ | -- | 7 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 3 | -- | |
| Turn-off Delay Time | $t_{\text{d}(\text{off})}$ | | -- | 30 | -- | |
| Turn-off Fall Time | t_f | | -- | 12 | -- | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Body Diode Current | I_S | $T_C = 25^\circ\text{C}$ | -- | -- | -4.2 | A |
| Body Diode Voltage | V_{SD} | $T_J = 25^\circ\text{C}, I_{\text{SD}} = -4\text{A}, V_{\text{GS}} = 0\text{V}$ | -- | -- | -1.2 | V |
| Reverse Recovery Charge | Q_{rr} | $I_F = -4\text{A}, V_{\text{GS}} = 0\text{V}$ $dI/dt = -100\text{A}/\mu\text{s}$ | -- | 8 | -- | nC |
| Reverse Recovery Time | T_{rr} | | -- | 14 | -- | ns |

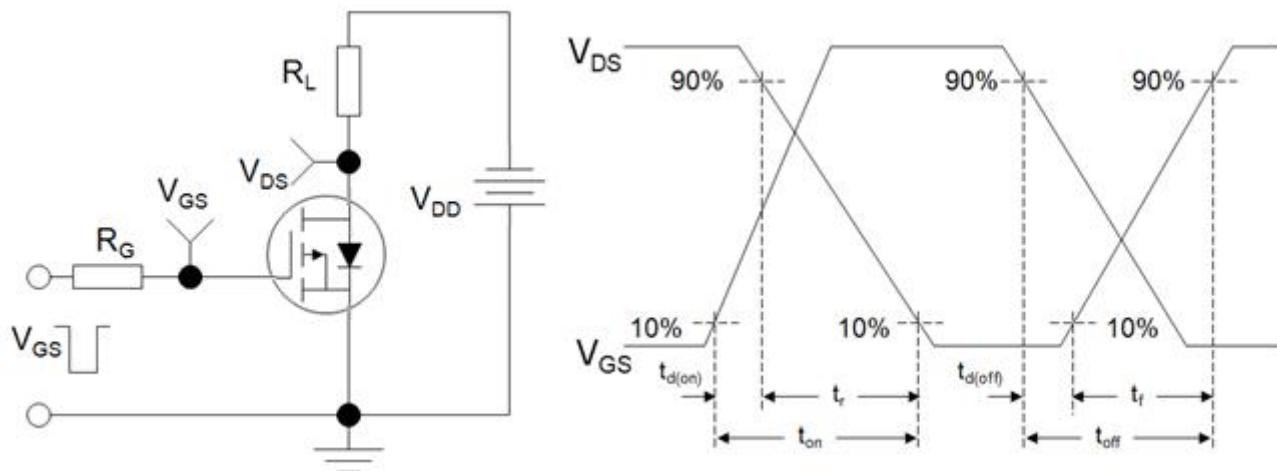
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

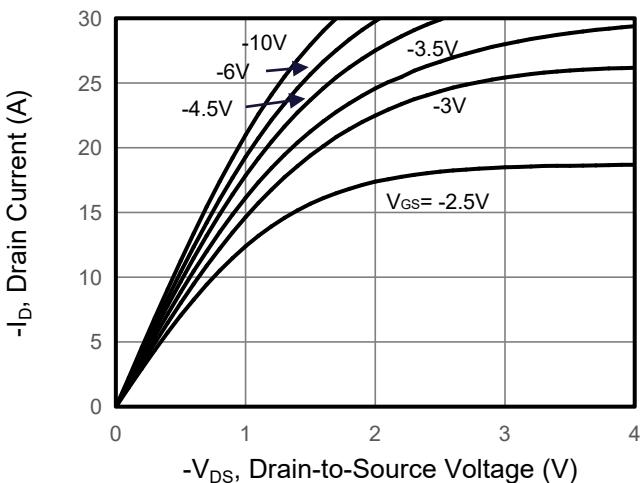


Figure 2. Transfer Characteristics

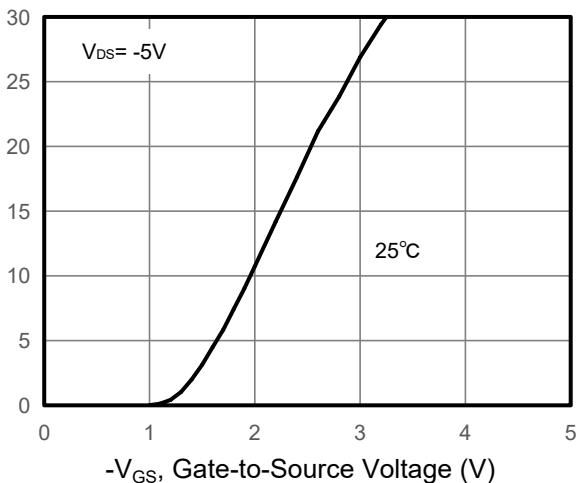


Figure 3. Drain Source On Resistance

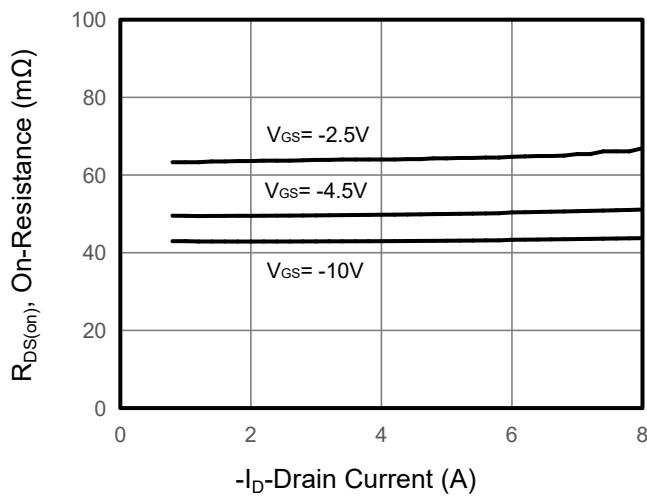


Figure 4. Gate Charge

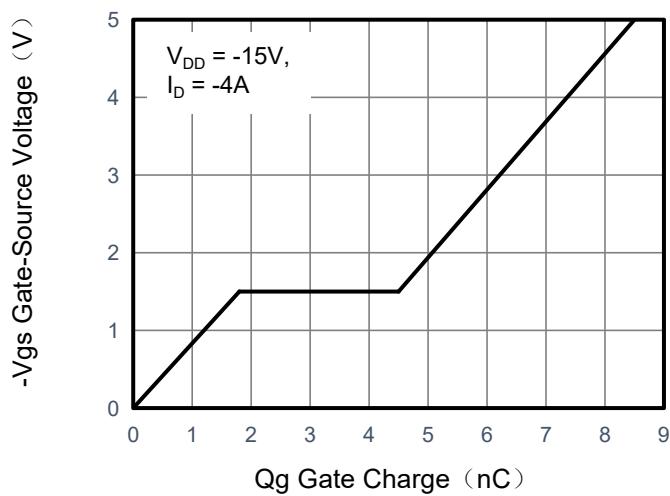


Figure 5. Capacitance

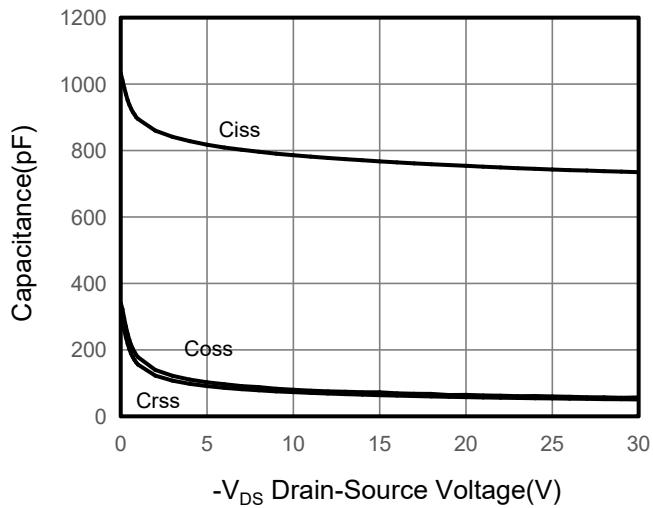
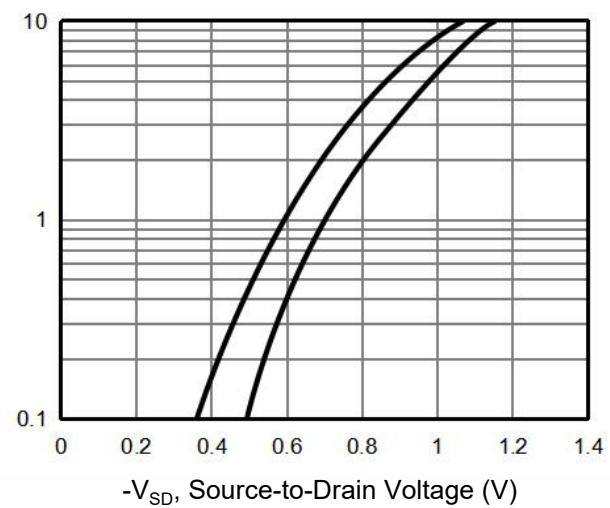


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

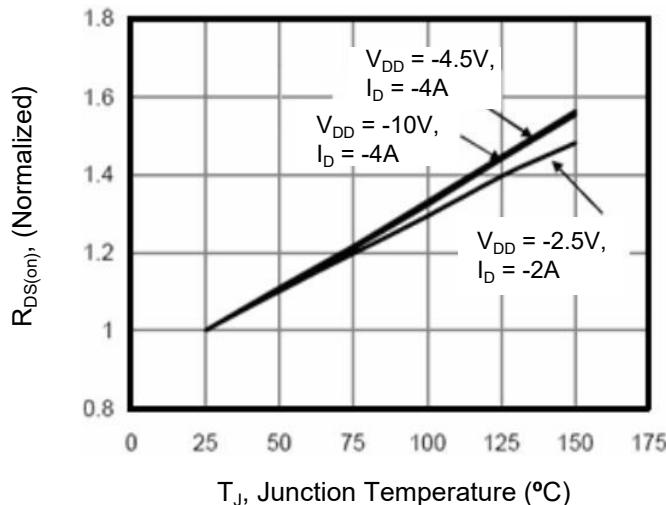


Figure 10. Safe Operation Area

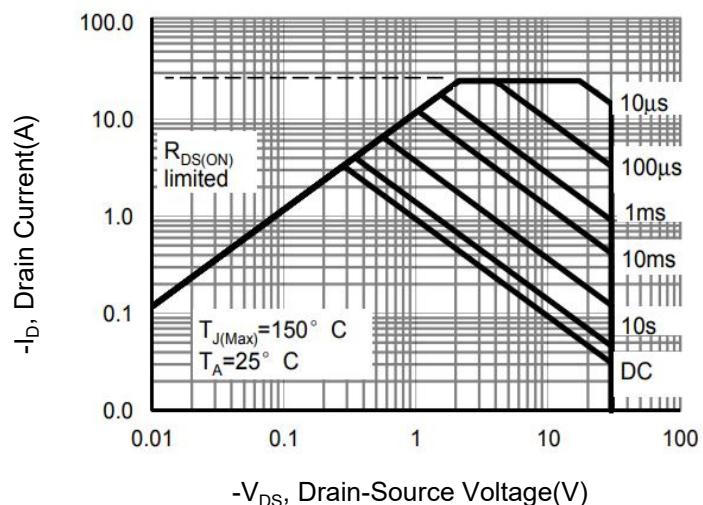
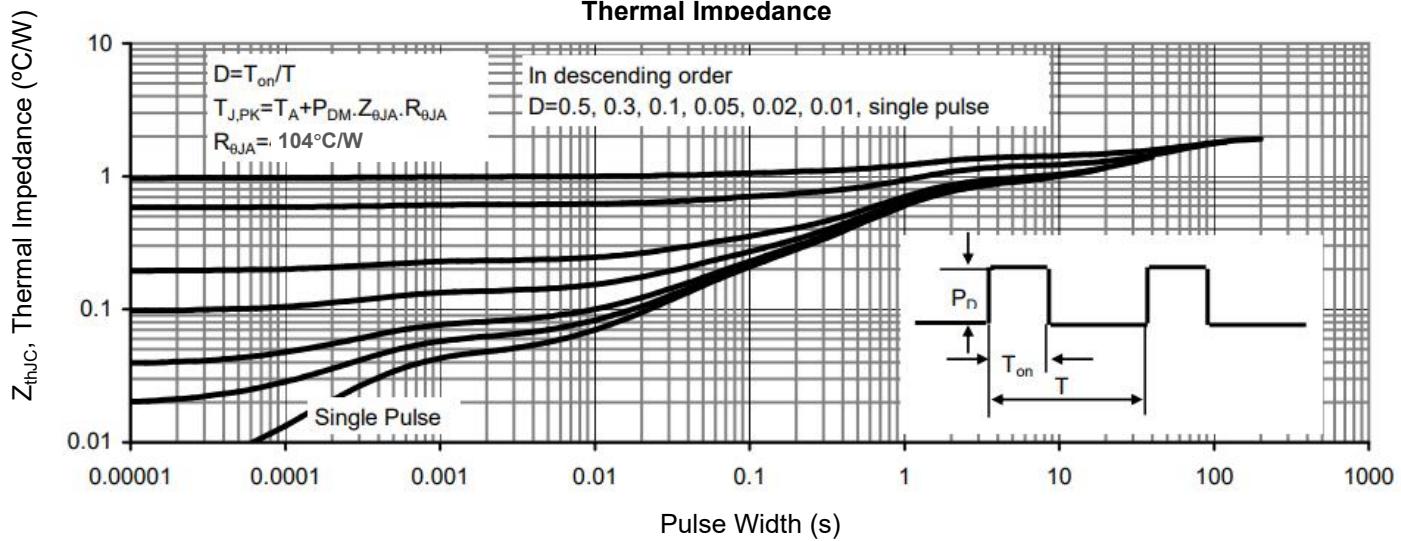
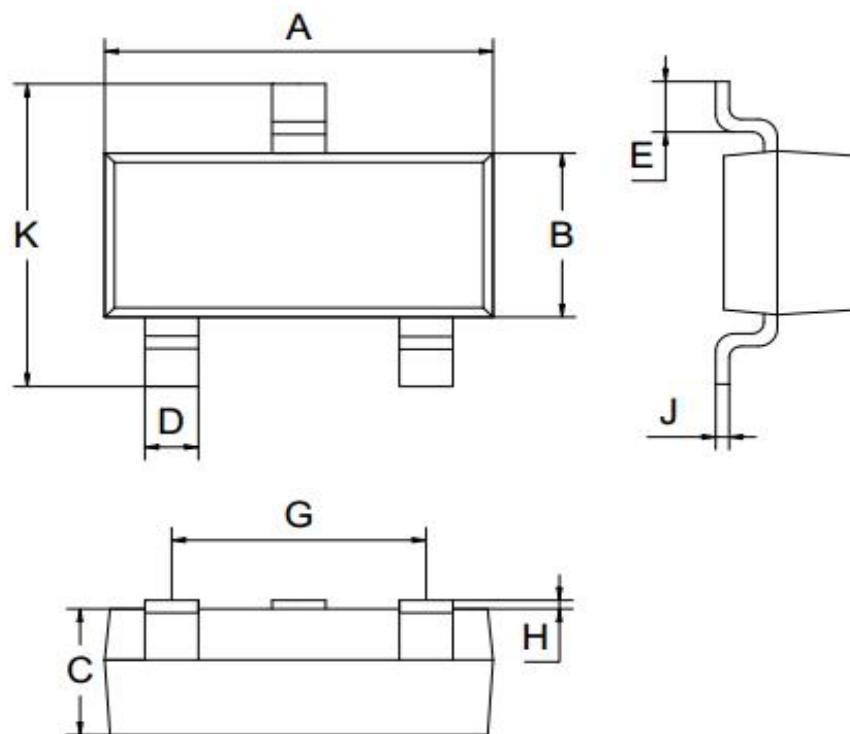


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



| SOT-23-3L | | | |
|----------------------|-------|-------|-------|
| Dim | MIN | NOM | MAX |
| A | 2.80 | 2.90 | 3.00 |
| B | 1.50 | 1.60 | 1.70 |
| C | 1.00 | 1.10 | 1.20 |
| D | 0.30 | 0.40 | 0.50 |
| E | 0.25 | 0.40 | 0.55 |
| G | 1.90 | | |
| H | 0.00 | - | 0.10 |
| J | 0.047 | 0.127 | 0.207 |
| K | 2.60 | 2.80 | 3.00 |
| All Dimensions in mm | | | |